

77.(New) A semiconductor device according to claim 76, wherein said first conductive layer comprises at least one selected from Ta, W, Ti and Mo, and said second conductive layer comprises Al or Cu.

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cont.

78.(New) A semiconductor device according to claim 76, wherein said semiconductor device is an EL display device.

79.(New) A semiconductor device according to claim 76, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera and a digital video disk player.

**REMARKS**

Applicants are amending the claims herewith to place them in better U.S. format. Applicants are also adding new claims. The fee for new claims has been calculated as shown below.

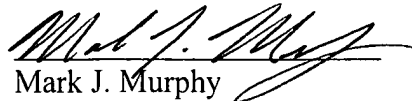
	Claims Remaining After Amendment		Highest Number Previously Paid For	Present Extra	Rate	Fee
Total	43	-	63	0	(small entity) x 9 (others) x 18	\$0.00
Independent	7	-	6	1	(small entity) x 42 (others) x 84	\$84.00
Multiple Dependent (None)					(small entity) + 140 (others) + 280	\$0.00
<b>TOTAL ADDITIONAL FEES</b>						<b>\$84.00</b>

Applicants are enclosing the \$84.00 fee for the additional independent claim. If any further fee is due, please charge our deposit account 50/1039.

Favorable consideration is earnestly solicited.

Respectfully submitted,

Date: 12-19-02

  
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Marked-up copy of the claims as amended:

**IN THE CLAIMS:**

Please amend the claims as follows:

3.(Amended) A semiconductor device according to claim 1, wherein said first conductive layer [is composed mainly of] comprises at least one selected from Ta, W, Ti and Mo, and said second conductive layer [is composed mainly of] comprises Al or Cu.

4.(Amended) A semiconductor device according to claim 1, wherein said first conductive layer comprises a conductive layer (A) containing nitrogen and at least one selected from Ta, W, Ti and Mo, a conductive layer (B) formed on said conductive layer (A) and [composed mainly of] comprising at least one selected from Ta, W, Ti and Mo, and a conductive layer (C) formed on regions where said conductive layer (B) does not contact said conductive layer (A) and containing nitrogen and at least one selected from Ta, W, Ti and Mo, and

wherein said second conductive layer comprises a conductive layer (D) [composed mainly of] comprising Al or Cu and a conductive layer (E) [composed mainly of] comprising at least one selected from Ta, W, Ti and Mo.

6.(Amended) A semiconductor device according to claim 1, wherein said first conductive layer comprises a conductive layer (A) containing nitrogen and at least one selected from Ta, W, Ti and Mo, a conductive layer (B) formed on said conductive layer (A) and [composed mainly of] comprising at least one selected from Ta, W, Ti and Mo and a conductive layer (C) formed on regions where said conductive layer (B) does not contact said conductive layer (A) and containing nitrogen and at least one selected from Ta, W, Ti and Mo,

wherein said second conductive layer comprises a conductive layer (D) [composed mainly of] comprising Al or Cu and a conductive layer (E) [composed mainly of] comprising at least one selected from Ta, W, Ti and Mo, and

wherein said conductive layer (C) and said conductive layer (D) are in contact at said connectors.

12.(Amended) A semiconductor device according to claim 10, wherein said first conductive layer [is composed mainly of] comprises at least one selected from Ta, W, Ti and Mo, and said second conductive layer [is composed mainly] comprises of Al or Cu.

13.(Amended) A semiconductor device according to claim 10, wherein said first conductive layer comprises a conductive layer (A) containing nitrogen and at least one selected from Ta, W, Ti and Mo, a conductive layer (B) formed on said conductive layer (A) and [composed mainly of] comprising at least one selected from Ta, W, Ti and Mo, and a conductive layer (C) formed on regions where said conductive layer (B) does not contact said conductive layer (A) and containing nitrogen and at least one selected from Ta, W, Ti and Mo, and

wherein said second conductive layer comprises a conductive layer (D) [composed mainly of] comprising Al or Cu and a conductive layer (E) [composed mainly of] comprising at least one selected from Ta, W, Ti and Mo.

15.(Amended) A semiconductor device according to claim 10, wherein said first conductive layer comprises a conductive layer (A) containing nitrogen and at least one selected from Ta, W, Ti and Mo, a conductive layer (B) formed on said conductive layer (A) and [composed mainly of]

comprising at least one selected from Ta, W, Ti and Mo and a conductive layer (C) formed on regions where said conductive layer (B) does not contact said conductive layer (A) and containing nitrogen and at least one selected from Ta, W, Ti and Mo, and

wherein said second conductive layer comprises a conductive layer (D) [composed mainly of] comprising Al or Cu and a conductive layer (E) [composed mainly of] comprising at least one selected from Ta, W, Ti and Mo, and

wherein said conductive layer (C) and said conductive layer (D) are in contact at said connectors.

21.(Amended) A semiconductor device according to claim 19, wherein said first conductive layer [is composed mainly of] comprises at least one selected from Ta, W, Ti and Mo, and said second conductive layer [is composed mainly of] comprises Al or Cu.

22.(Amended) A semiconductor device according to claim 19, wherein said first conductive layer comprises a conductive layer (A) containing nitrogen and at least one selected from Ta, W, Ti and Mo, a conductive layer (B) formed on said conductive layer (A) and [composed mainly of] comprising at least one selected from Ta, W, Ti and Mo, and a conductive layer (C) formed on regions where said conductive layer (B) does not contact said conductive layer (A) and containing nitrogen and at least one selected from Ta, W, Ti and Mo, and

wherein said second conductive layer comprises a conductive layer (D) [composed mainly of] comprising Al or Cu and a conductive layer (E) [composed mainly of] comprising at least one selected from Ta, W, Ti and Mo.

24.(Amended) A semiconductor device according to claim 19, wherein said first conductive layer comprises a conductive layer (A) containing nitrogen and at least one selected from Ta, W, Ti and Mo, a conductive layer (B) formed on said conductive layer (A) and [composed mainly of] comprising at least one selected from Ta, W, Ti and Mo and a conductive layer (C) formed on regions where said conductive layer (B) does not contact said conductive layer (A) and containing nitrogen and at least one selected from Ta, W, Ti and Mo,

wherein said second conductive layer comprises a conductive layer (D) [composed mainly of] comprising Al or Cu and a conductive layer (E) [composed mainly of] comprising at least one selected from Ta, W, Ti and Mo, and

wherein said conductive layer (C) and said conductive layer (D) are in contact at said connectors.

Cancel Claims 28-63

Please add the following new claims:

64.(New) A semiconductor device comprising:

a semiconductor layer over a substrate, said semiconductor layer comprising a pair of impurity regions and a channel region interposed therebetween;

a gate electrode over said channel region with a gate insulating film interposed therebetween, said gate electrode comprising a first conductive layer; and

a gate wiring in contact with said gate electrode, said gate wiring comprising a second conductive layer,

wherein said gate wiring is provided outside said channel region.

65.(New) A semiconductor device according to claim 64, wherein said first conductive layer comprises at least one selected from Ta, W, Ti and Mo, and said second conductive layer comprises Al or Cu.

66.(New) A semiconductor device according to claim 64, wherein said semiconductor device is an EL display device.

67.(New) A semiconductor device according to claim 64, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera and a digital video disk player.

68.(New) A semiconductor device comprising:

a semiconductor layer over a substrate, said semiconductor layer comprising a pair of impurity regions and a channel region interposed therebetween;

a gate electrode over said channel region with a gate insulating film interposed therebetween, said gate electrode comprising a first conductive layer; and

a gate wiring in contact with said gate electrode, said gate wiring comprising a second conductive layer which is a different material from said first conductive layer,

wherein said gate wiring is provided outside said channel region.

69.(New) A semiconductor device according to claim 68, wherein said first conductive layer comprises at least one selected from Ta, W, Ti and Mo, and said second conductive layer comprises Al or Cu.

70.(New) A semiconductor device according to claim 68, wherein said semiconductor device is an EL display device.

71.(New) A semiconductor device according to claim 68, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera and a digital video disk player.

72.(New) A semiconductor device comprising:  
a semiconductor layer over a substrate, said semiconductor layer comprising a pair of impurity regions and a channel region interposed therebetween;  
a gate electrode over said channel region with a gate insulating film interposed therebetween, said gate electrode comprising a first conductive layer; and  
a gate wiring overlapping said gate electrode, said gate wiring comprising a second conductive layer,  
wherein said gate wiring is provided outside said channel region.

73.(New) A semiconductor device according to claim 72, wherein said first conductive layer comprises at least one selected from Ta, W, Ti and Mo, and said second conductive layer comprises Al or Cu.



74.(New) A semiconductor device according to claim 72, wherein said semiconductor device is an EL display device.

75.(New) A semiconductor device according to claim 72, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera and a digital video disk player.

76.(New) A semiconductor device comprising:  
a semiconductor layer over a substrate, said semiconductor layer comprising a pair of impurity regions and a channel region interposed therebetween;  
a gate electrode over said channel region with a gate insulating film interposed therebetween, said gate electrode comprising a first conductive layer; and  
a gate wiring overlapping said gate electrode, said gate wiring comprising a second conductive layer which is a different material from said first conductive layer,  
wherein said gate wiring is provided outside said channel region.

77.(New) A semiconductor device according to claim 76, wherein said first conductive layer comprises at least one selected from Ta, W, Ti and Mo, and said second conductive layer comprises Al or Cu.

78.(New) A semiconductor device according to claim 76, wherein said semiconductor device is an EL display device.

79.(New) A semiconductor device according to claim 76, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera and a digital video disk player.